

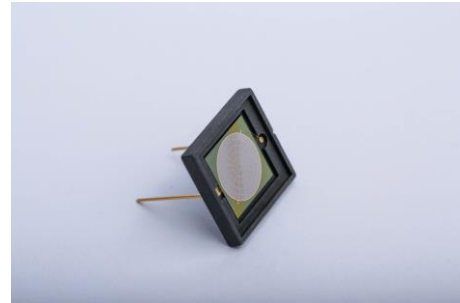


# EUV photodiode

Model **SCT-EUV64**

## General Features:

- SiC-based extreme ultraviolet (EUV) photodiode
- Excellent stability under high fluence EUV exposure
- Photovoltaic mode operation
- Visible blind and low dark current
- High detection efficiency for 13.5 nm EUV radiation
- Ceramic package

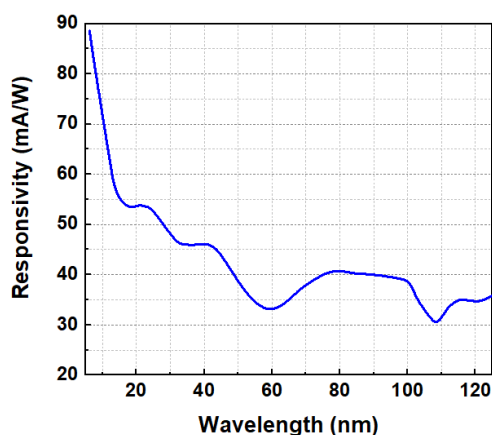


**Applications:** EUV radiation monitoring and flux measurement

## Specifications:

Parameters	Symbol	Value	Unit
<b>Maximum ratings</b>			
Operation temperature range	$T_{opt}$	-20-80	°C
Storage temperature range	$T_{sto}$	-55-90	°C
Soldering temperature (3 s)	$T_{sol}$	260	°C
Maxium reverse voltage	$V_{r-max}$	-20	V
<b>Electro-Optical characteristics (25 °C)</b>			
Chip size	A	63.5	mm <sup>2</sup>
Spectral response range		5-125	nm
Responsivity (@ 13.5 nm)	R	58	mA/W
Dark current ( $V_r = -1V$ )	$I_d$	< 100	pA
Shunt resistance (@±10mV)	$R_{sh}$	>10	G
Capacitance (@ 0 V and 1 MHz)	$C_p$	2.4	nF
Rise Time ( $V_r=0 V, R_L \geq 2k\Omega$ )	$t_r$	< 2	S

## Spectral response



## Package dimensions (unit: mm)

